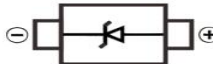


SOD-523 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	SD103AWT	SD103BWT	SD103CWT
Pin 管脚			
Mark 打标	S4	S5	S6

Absolute Maximum Ratings 最大额定值

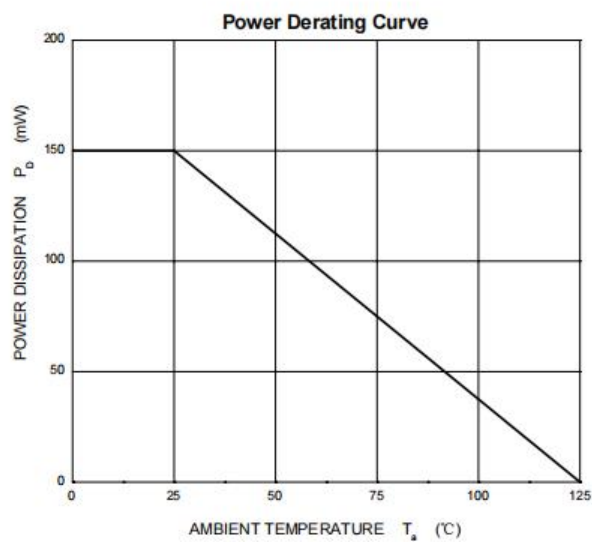
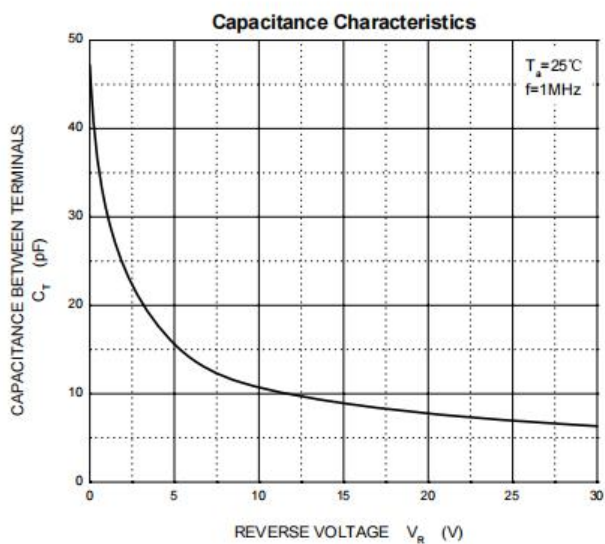
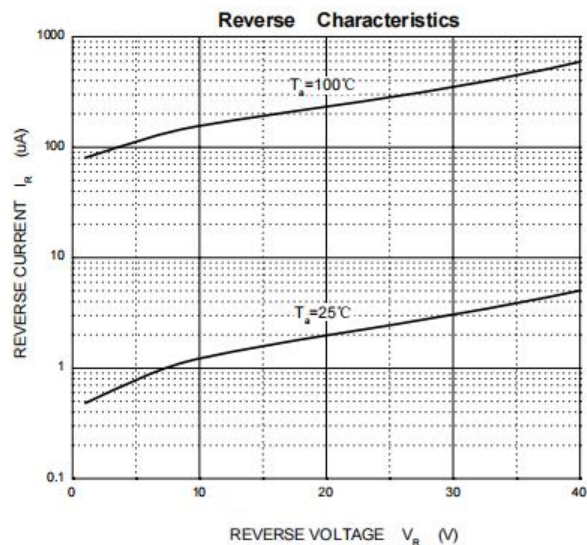
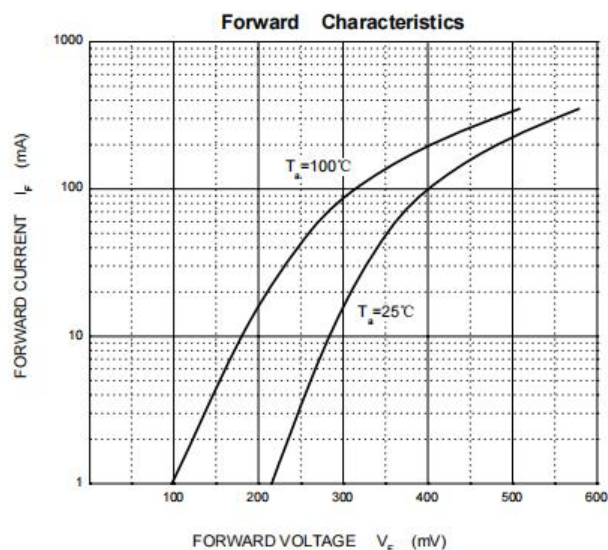
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Reverse Voltage/ SD103AWT	V_R/V_{RRM}	40	V
Repetitive Reverse Voltage SD103BWT		30	
反向电压/重复反向电压 SD103CWT		20	
Forward Work Current 正向工作电流	I_o	350	mA
Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	2000	mA
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-65to+125 $^{\circ}C$	

Electrical Characteristics 电特性

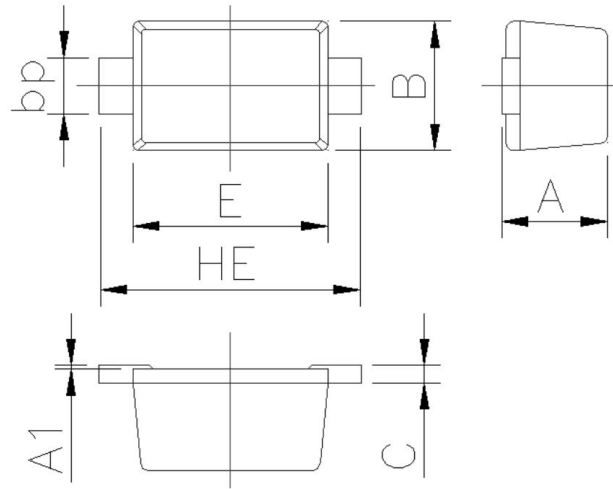
($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage SD103AWT	$V_{(BR)}$	40	—	V
反向击穿电压 SD103BWT		30		
($I_R=10\mu A$) SD103CWT		20		
Reverse Leakage Current($V_R=30V$) SD103AWT	I_R	—	5	μA
反向漏电流($V_R=20V$) SD103BWT			5	
($V_R=10V$) SD103CWT			5	
Forward Voltage($I_F=20mA$)	V_F	—	0.37	V
正向电压($I_F=200mA$)			0.6	
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_D	—	50	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	10	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70